Unit: mm

TOSHIBA GTR Module Silicon N Channel IGBT

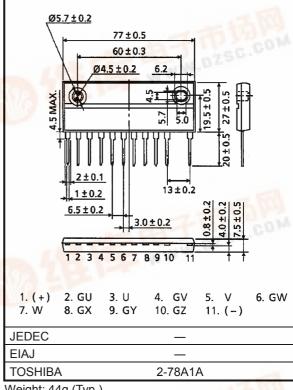
MP6754

High Power Switching Applications **Motor Control Applications**

- The electrodes are isolated from case.
- 6 IGBTs are built into 1 package.
- Enhancement-mode
- Low saturation voltage

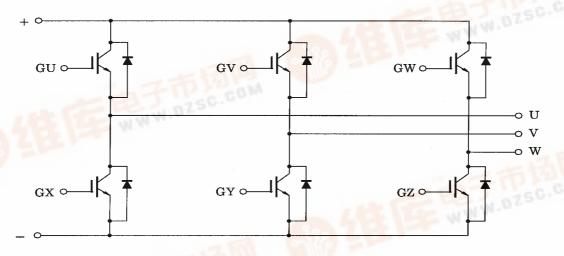
: $V_{CE (sat)} = 4.0 V (Max) (I_{C} = 10A)$

High speed : $tf = 0.35\mu s$ (Max) (IC = 10A) $t_{rr} = 0.15 \mu s \text{ (Max) (IF} = 10 \text{A)}$



Weight: 44g (Typ.)

Equivalent Circuit



• TOSHIBA is continually working to improve the quality and reliability of its products. Nevertheless, semiconductor devices in general can malfunction or fail due to their inherent electrical sensitivity and vulnerability to physical stress. It is the responsibility of the buyer, when utilizing TOSHIBA products, to comply with the standards of safety in making a safe design for the entire system, and to avoid situations in which a malfunction or failure of such TOSHIBA products could cause loss of human life, bodily injury or

damage to property.

In developing your designs, please ensure that TOSHIBA products are used within specified operating ranges as set forth in the most recent TOSHIBA products specifications. Also, please keep in mind the precautions and conditions set forth in the "Handling Guide for Semiconductor Devices," or "TOSHIBA Semiconductor Reliability Handbook" etc..

The TOSHIBA products listed in this document are intended for usage in general electronics applications (computer, personal equipment, office equipment, measuring equipment, industrial robotics, domestic appliances, etc.). These TOSHIBA products are

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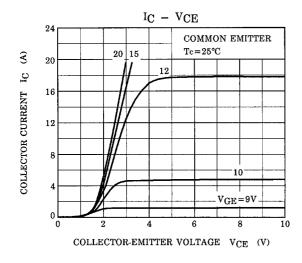
Maximum Ratings (Ta = 25°C)

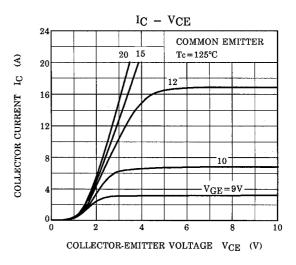
Characteristic		Symbol	Rating	Unit	
Collector-emitter voltage		V _{CES}	600	V	
Gate-emitter voltage		V _{GES}	± 20	V	
Collector current	DC	IC	10	Α	
	1ms	I _{CP}	20		
Forward current	DC	I _F	10	Α	
	1ms	I _{FM}	20		
Collector power dissipation (Tc = 25°C)		P _C	40	W	
Junction temperature		Tj	150	°C	
Storage temperature range		T _{stg}	- 40 ~ 125	°C	
Isolation voltage		V _{ISOL}	2500 (AC 1 minute)	V	
Screw torque		_	1.5	N·m	

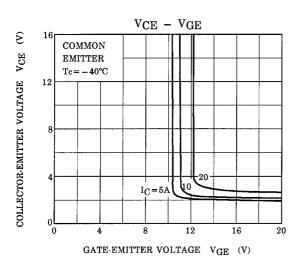
Electrical Characteristics (Ta = 25°C)

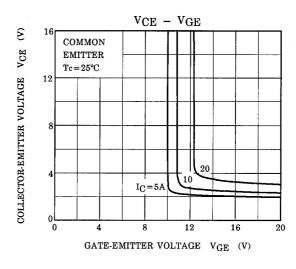
Characteristic		Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current		I _{GES}	V _{GE} = ± 20V, V _{CE} = 0	_	_	± 500	nA
Collector cut-off current		I _{CES}	V _{CE} = 600V, V _{GE} = 0	_	_	1.0	mA
Gate-emitter cut-off voltage		V _{GE (off)}	I _C = 10mA, V _{CE} = 5V	6.0	_	9.0	V
Collector-emitter saturation voltage		V _{CE} (sat)	I _C = 10A, V _{GE} = 15V	_	3.0	4.0	V
Input capacitance		C _{ies}	V _{CE} = 10V, V _{GE} = 0, f = 1MHz	_	620	_	pF
Switching time	Rise time	t _r	15V 100Ω 300V	_	0.3	0.6	μs
	Turn-on time	t _{on}		_	0.4	0.8	
	Fall time	t _f		_	0.2	0.35	
	Turn-off time	t _{off}		_	0.4	0.8	
Forward voltage		V _F	I _F = 10A, V _{GE} = 0	_	1.7	2.5	V
Reverse recovery time		t _{rr}	I _F = 10A, V _{GE} = -10V di / dt = 100A / μs	_	0.08	0.15	μs
Thermal resistance		R _{th (j-c)}	Transistor	— — 3.09		°C/W	
			Diode	_	_	3.09]

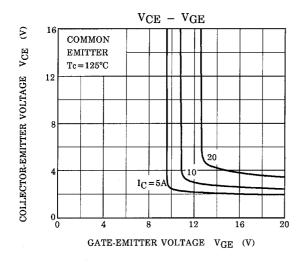
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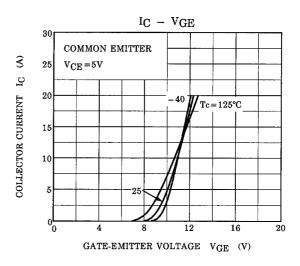


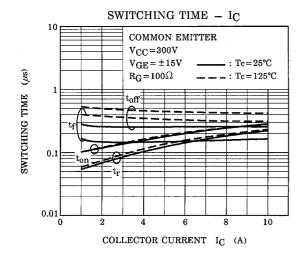


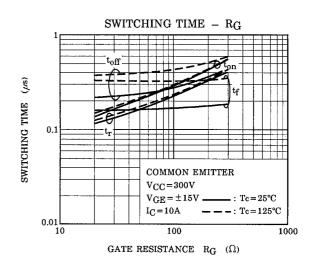


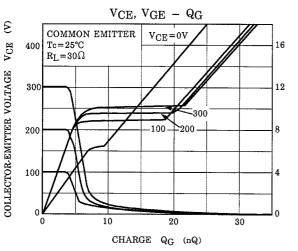


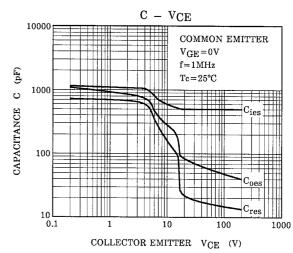












3

GATE-EMITTER VOLTAGE VGE

